Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	287	semiconductor and substrate and area with mask and resist and impurity and doping and acceleration adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:21
L7	195	semiconductor and substrate and area with mask and resist and impurity and doping and acceleration adj voltage and @ad<"20021024"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 19:30
L8	10	semiconductor and substrate and area with mask and resist and impurity and doping and acceleration adj voltage and (percent or (per adj cent) or ".%. ") and @ad<"20021024"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:07
L9	0	(semiconductor and substrate and area with mask and resist and impurity and doping and (percent or (per adj cent) or ".%.")).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:12
L10	2	(semiconductor and substrate and area with mask and resist and impurity and doping).clm.	US-PGPUB	OR	ON	2005/07/23 20:10
L11	0	(semiconductor and substrate and area with mask and resist and impurity and doping and (percent or (per adj cent) or ".%.")).clm.	US-PGPUB	OR	ON	2005/07/23 20:13
L12	1096	(438/514).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:16
L13	878	(438/510).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:16
L14	220	(438/517).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:16
L15	158	(438/552).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:17

L16	378	(438/546).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:17
L17	193	(438/545).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:17
L18	140	(438/555).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:17
L19	390	(438/20).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:17
L20	826	(438/30).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:17
L21	842	(438/48).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:17
L22	1400	(438/149).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:18
L23	1898	(257/72).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:18
L24	1362	(257/79).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:18
L25	1065	(257/82).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:18
L26	839	(257/88).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/23 20:18
L27	1	l6 and l12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:18

L28	0	I6 and I13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:19
L29	1	I6 and I14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:19
L30	0	I6 and I15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:19
L31	0	I6 and I16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:19
L32	0	I6 and I17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:19
L33	0	I6 and I18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:19
L34	0	I6 and I19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:19
L35	5	I6 and I20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:19

L36	4	I6 and I21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:19
L37	18	I6 and I22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:19
L38	36	I6 and I23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:20
L39	3	I6 and I24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:20
L40	1	I6 and I25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:20
L41	0	I6 and I26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:20
L42	252776	semiconductor and substrate and area or coverage with mask and resist and impurity and doping	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:21
L43	1905	semiconductor and substrate and (area or coverage) with mask and resist and impurity and doping	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22

L44	6	I43 and I12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L45	2	I43 and I13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L46	11	I43 and I14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L47	5	I43 and I15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L48	6	I43 and I16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L49	6	I43 and I17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L50	4	I43 and I18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L51	5	I43 and I19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22

L52	11	I43 and I20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L53	11	I43 and I21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L54	54	I43 and I22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L55	66	I43 and I23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L56	9	I43 and I24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:22
L57	2	I43 and I25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:23
L58	4	I43 and I26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 20:23